

Title (en)  
Method of preparing a semiconductor substrate

Title (de)  
Verfahren zur Herstellung eines Halbleitersubstrats

Title (fr)  
Procédé de fabrication d'un substrat semi-conducteur

Publication  
**EP 0553856 B1 20020417 (EN)**

Application  
**EP 93101417 A 19930129**

Priority  

- JP 4058492 A 19920131
- JP 4630392 A 19920131
- JP 4630492 A 19920131
- JP 4630592 A 19920131

Abstract (en)  
[origin: EP0553856A2] A semiconductor substrate comprises an insulating layer and a compound semiconductor monocrystal thin film formed on said insulating layer, the thermal expansion coefficient of said insulating layer being in the range of 60%-140% of that of said monocrystal thin film.

IPC 1-7  
**H01L 21/76**; **H01L 21/20**

IPC 8 full level  
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CPC (source: EP US)  
**H01L 21/02381** (2013.01 - EP US); **H01L 21/0245** (2013.01 - EP US); **H01L 21/02463** (2013.01 - EP US); **H01L 21/02507** (2013.01 - EP US); **H01L 21/02546** (2013.01 - EP US); **H01L 21/0262** (2013.01 - EP US); **H01L 21/30604** (2013.01 - EP US); **H01L 21/76251** (2013.01 - EP US); **H01L 21/76256** (2013.01 - EP US); **H01L 31/1892** (2013.01 - EP US); **Y02E 10/50** (2013.01 - US); **Y10S 438/96** (2013.01 - EP US)

Cited by  
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**EP 93101417 A 19930129**; DE 69331816 T 19930129; EP 01119915 A 19930129; US 30126394 A 19940906